

simultaneously removing the photoresist layer and the conductive layer. The photoresist can be a positive photoresist or a negative photoresist. The conductive layer can be formed from a metal or metal oxide. Also, the step of simultaneously removing the photoresist layer and the conductive layer is performed by etching.

[0035] The foregoing and other objects, features, aspects and advantages of the invention will become more apparent from the following detailed description of the invention when taken in conjunction with the accompanying drawings.

BRIEF DESCRIPTION OF THE DRAWINGS

[0036] The accompanying drawings, which are included to provide a further understanding of the invention and are incorporated in and constitute a part of this specification, illustrate embodiments of the invention and together with the description serve to explain the principles of the invention.

[0037] Figures 1A to 1E are views showing manufacturing processes of a thin film transistor of an LCD device using a 5-mask process in accordance with the related art.

[0038] Figures 2A to 2H are views showing manufacturing processes of the TFT of an LCD device using a 4-mask process in accordance with the conventional art.

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[0039] Figures 3A to 3⁵ are views showing manufacturing processes of a TFT of an LCD device using a 3-mask process according to the invention.

DETAILED DESCRIPTION

[0040] Advantages of the invention will become more apparent from the